

#### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Collector Current – Continuous	Ι <sub>C</sub>	200	mA

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)	D	0.75	W	
ower Dissipation PD (Note 6)		PD	1.2	vv	
Thermal Desistance, lunction to Ambient Air	(Note 5)		166	•C/W	
Thermal Resistance, Junction to Ambient Air	(Note 6)	R <sub>0</sub> JA	104		
Operating and Storage Temperature Range	•	T <sub>i</sub> , T <sub>STG</sub>	-55 to +150	°C	

### ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

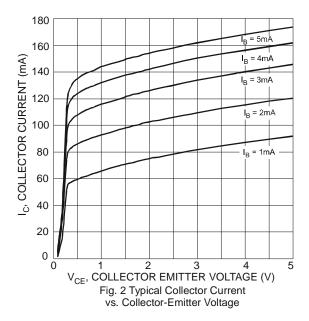
 For a device mounted with the exposed collector pad on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
Same as note (5), except the device is mounted with the exposed collector pad on 25mm x 25mm 1oz copper.
Refer to JEDEC specification JESD22-A114 and JESD22-A115. Notes:

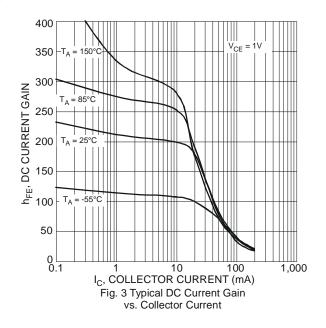


#### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)			•	•	·	
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	60		V	$I_{C} = 10 \mu A, I_{E} = 0$	
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	40		V	$I_{\rm C} = 1.0 {\rm mA}, I_{\rm B} = 0$	
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6.0		V	$I_{E} = 10 \mu A, I_{C} = 0$	
Collector Cutoff Current	I <sub>CEX</sub>		50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$	
Base Cutoff Current	I <sub>BL</sub>		50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$	
ON CHARACTERISTICS (Note 7)				_	-	
DC Current Gain	h <sub>FE</sub>	40 70 100 60 30	 300 	_	$\begin{split} I_{C} &= 100 \mu A, \ V_{CE} = 1.0 V \\ I_{C} &= 1.0 m A, \ V_{CE} = 1.0 V \\ I_{C} &= 10 m A, \ V_{CE} = 1.0 V \\ I_{C} &= 50 m A, \ V_{CE} = 1.0 V \\ I_{C} &= 100 m A, \ V_{CE} = 1.0 V \end{split}$	
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	0.20 0.30	V	$I_{C} = 10mA, I_{B} = 1.0mA$ $I_{C} = 50mA, I_{B} = 5.0mA$	
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	0.65	0.85 0.95	V	$I_{C} = 10mA, I_{B} = 1.0mA$ $I_{C} = 50mA, I_{B} = 5.0mA$	
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C <sub>obo</sub>		4.0	pF	$V_{CB} = 5.0V, f = 1.0MHz, I_E = 0$	
Input Capacitance	C <sub>ibo</sub>		8.0	pF	$V_{EB} = 0.5V, f = 1.0MHz, I_{C} = 0$	
Input Impedance	h <sub>ie</sub>	1.0	10	kΩ		
Voltage Feedback Ratio	h <sub>re</sub>	0.5	8.0	x 10 <sup>-4</sup>	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1.0mA, f = 1.0kHz	
Small Signal Current Gain	h <sub>fe</sub>	100	400	—	$V_{CE} = 10V, 1C = 1.000A, 1 = 1.00012$	
Output Admittance	h <sub>oe</sub>	1.0	40	μS		
Current Gain-Bandwidth Product	f <sub>T</sub>	300		MHz	$V_{CE} = 20V, I_{C} = 10mA, f = 100MHz$	
Noise Figure	NF	—	5.0	dB	$\label{eq:Vce} \begin{split} V_{CE} &= 5.0V, \ I_C = 100 \mu A, \\ R_S &= 1.0 k \Omega, \ f = 1.0 k Hz \end{split}$	
SWITCHING CHARACTERISTICS					-	
Delay Time	t <sub>d</sub>		35	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$	
Rise Time	tr		35	ns	$V_{BE(off)} = -0.5V, I_{B1} = 1.0mA$	
Storage Time	t <sub>s</sub>		200	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$	
Fall Time	t <sub>f</sub>		50	ns	$I_{B1} = -I_{B2} = 1.0 \text{mA}$	

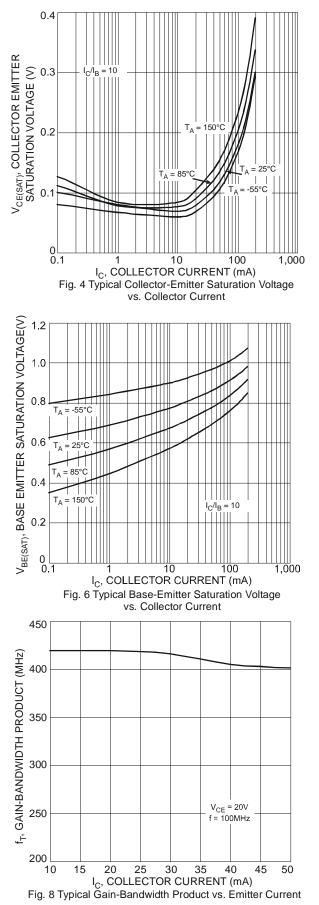
Notes: 7. Measured under pulsed condition. Pulse width =  $300\mu$ s. Duty cycle  $\leq 2\%$ .

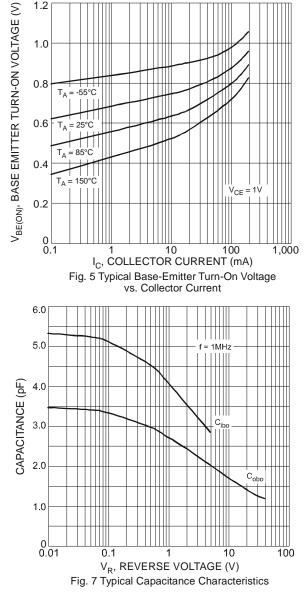




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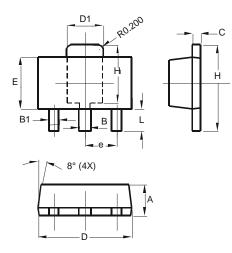
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**DXT3904** 



### **Package Outline Dimensions**

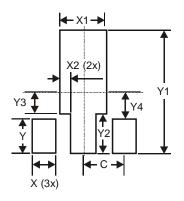
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT89				
Dim	Min	Max		
Α	1.40	1.60		
В	0.44	0.62		
B1	0.35	0.54		
С	0.35	0.44		
D	4.40	4.60		
D1	1.62	1.83		
Е	2.29	2.60		
е	1.50 Typ			
н	3.94	4.25		
H1	2.63	2.93		
L	0.89	1.20		
All Dimensions in mm				

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Х	0.900
X1	1.733
X2	0.416
Y	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
С	1.500



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